

Koji Ito

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Body doping dependence of field-effect mobility in both n- and p-channel 4H-SiC metal-oxide-semiconductor field-effect transistors with nitrated gate oxides. Applied Physics Express, 2022, 15, 036503.	1.1	4
2	Impact of post-nitridation annealing in CO ₂ ambient on threshold voltage stability in 4H-SiC metal-oxide-semiconductor field-effect transistors. Applied Physics Express, 2022, 15, 061003.	1.1	2
3	Mobility enhancement in heavily doped 4H-SiC (0001), (112̄,0), and (11̄,00) MOSFETs via an oxidation-minimizing process. Applied Physics Express, 2022, 15, 071001.	1.1	9
4	Effect of quantum confinement on the defect-induced localized levels in 4H-SiC(0001)/SiO ₂ systems. Journal of Applied Physics, 2020, 128, .	1.1	13
5	Design and formation of SiC (0001)/SiO ₂ interfaces via Si deposition followed by low-temperature oxidation and high-temperature nitridation. Applied Physics Express, 2020, 13, 091003.	1.1	38
6	Influence of vacuum annealing on interface properties of SiC (0001) MOS structures. Japanese Journal of Applied Physics, 2019, 58, 078001.	0.8	2
7	Reduction of interface state density in SiC (0001) MOS structures by low-oxygen-partial-pressure annealing. Applied Physics Express, 2019, 12, 031001.	1.1	15